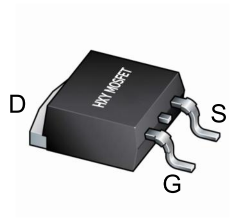
30N03A

N-Channel Enhancement Mode MOSFET

Description

The 30N03A uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO252-2L

General Features

V_{DS} = 30V I_D =100 A

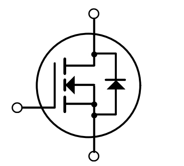
$R_{DS(ON)}$ < 5mΩ @ V_{GS}=10V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
30N03A	TO252-2L	100N03DXXX YYYY	2500

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating		Units
VDS	Drain- Source Voltage	30		V
VGS	Gate-Source Voltage	±20		V
I_D@T_C=25˚C	Continuous Drain Current, V_{GS} @ 10V[1]	100		A
I_D@T_C=100˚C	Continuous Drain Current, V_{GS} @ 10V[1]	57		A
I_D@T_A=25˚C	Continuous Drain Current, V_{GS} @ 10V[1]	27	17	A
I_D@T_A=70˚C	Continuous Drain Current, V_{GS} @ 10V[1]	23	14.5	A
I_{DM}	Pulsed Drain Current[2]	160		A
EAS	Single Pulse Avalanche Energy[3]	115.2		mJ
I_{AS}	Avalanche Current	48		A
P_D@T_C=25˚C	Total Power Dissipation[4]	53		W
P_D@T_A=25˚C	Total Power Dissipation[4]	6	2.4	W
T_{STG}	Storage Temperature Range	-55 to 175		˚C
T_J	Operating Junction Temperature Range	-55 to 175		˚C
$R_{θJA}$	Thermal Resistance Junction-ambient (Steady State)[1]	62		˚C/W
$R_{θJA}$	Thermal Resistance Junction-Ambient [1] (t ≤10s)	25		˚C/W
$R_{θJC}$	Thermal Resistance Junction-Case[1]	2.8		˚C/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25°C , I_D=1mA	---	0.028	---	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=30A	---	3.8	5.5	mΩ
		V_{GS}=4.5V , I_D=15A	---	7.5	9	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	1.5	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-6.16	---	mV/°C
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25°C	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=55°C	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=30A	---	22	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.7	3.4	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=15V , V_{GS}=4.5V , I_D=15A	---	20	---	nC
Q_{gs}	Gate-Source Charge		---	7.6	---	
Q_{gd}	Gate-Drain Charge		---	7.2	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GS}=10V , R_G=3.3 I_D=15A	---	7.8	---	ns
T_r	Rise Time		---	15	---	
$T_{d(off)}$	Turn-Off Delay Time		---	37.3	---	
T_f	Fall Time		---	10.6	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	2295	---	pF
C_{oss}	Output Capacitance		---	267	---	
C_{rss}	Reverse Transfer Capacitance		---	210	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	80	A
I_{SM}	Pulsed Source Current[2,5]		---	---	160	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25°C	---	---	1	V
t_{rr}	Reverse Recovery Time	IF=30A , dI/dt=100A/µs , T_J=25°C	---	14	---	nS
Q_{rr}	Reverse Recovery Charge		---	5	---	nC

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width .The EAS data shows Max. rating .
3.The test cond≦ 300us , duty cycle ition is $V_{DD=25}$≦V,V 2%$_{GS}$ =10V,L=0.1mH,I_{AS}=53.8A
4.The power dissipation is limited by 175°C junction temperature
5.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

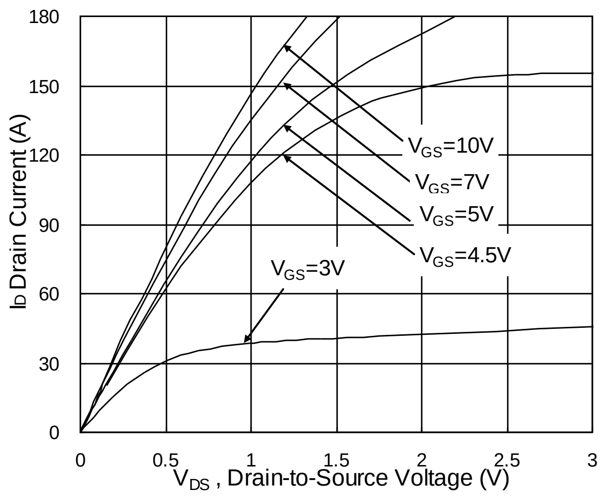


Fig.1 Typical Output Characteristics

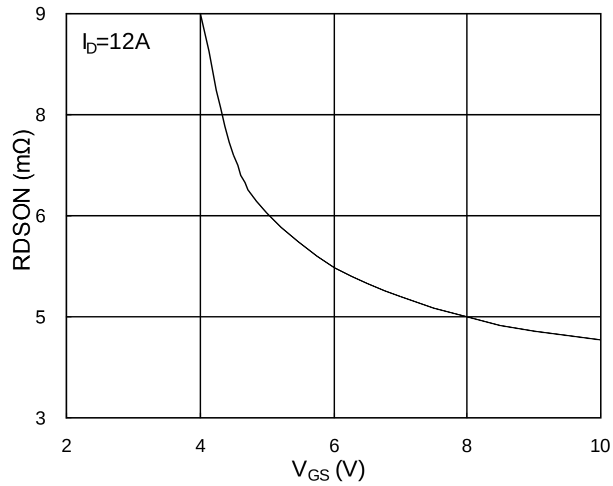


Fig.2 On-Resistance vs. G-S Voltage

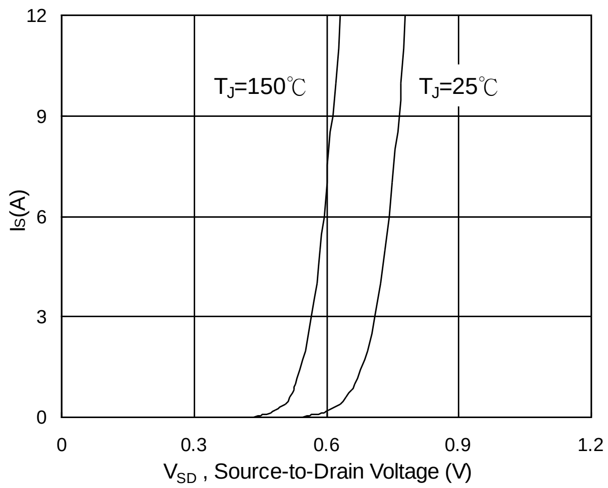


Fig.3 Forward Characteristics of Reverse

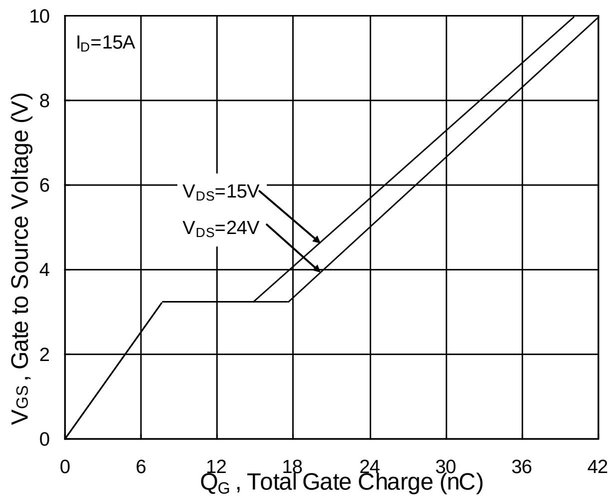


Fig.4 Gate-Charge Characteristics

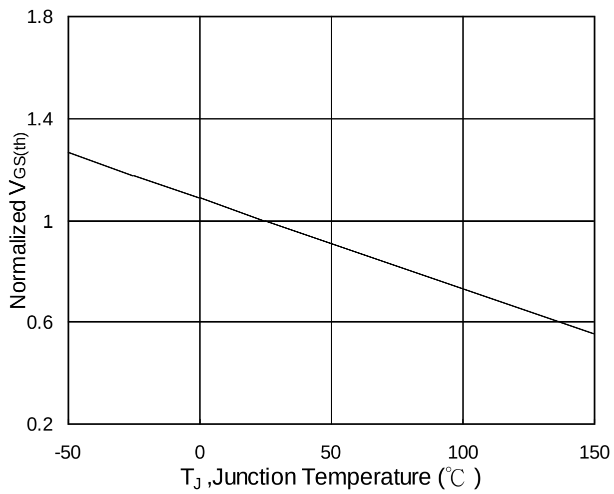


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

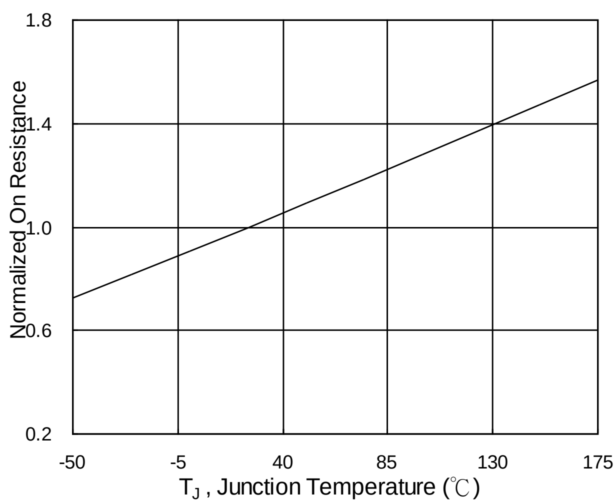


Fig.6 Normalized R_{DSON} vs. T_J

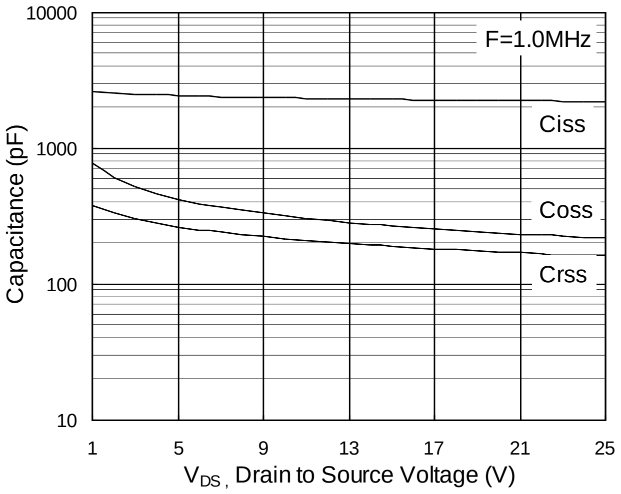


Fig.7 Capacitance

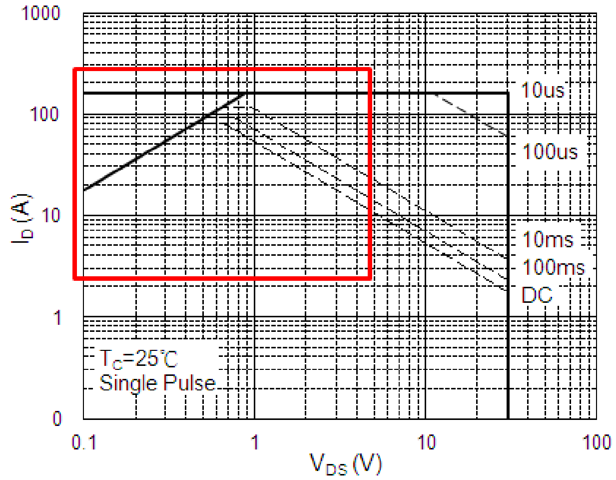


Fig.8 Safe Operating Area

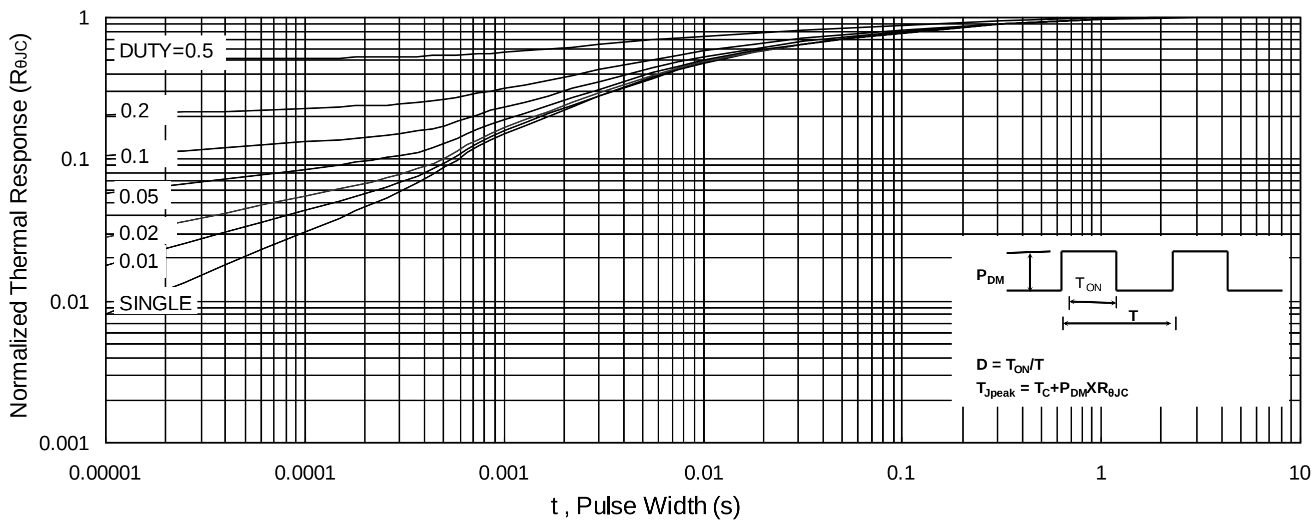


Fig.9 Normalized Maximum Transient Thermal Impedance

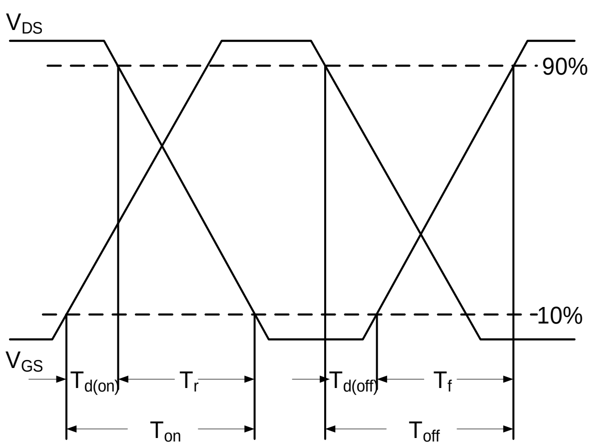


Fig.10 Switching Time Waveform

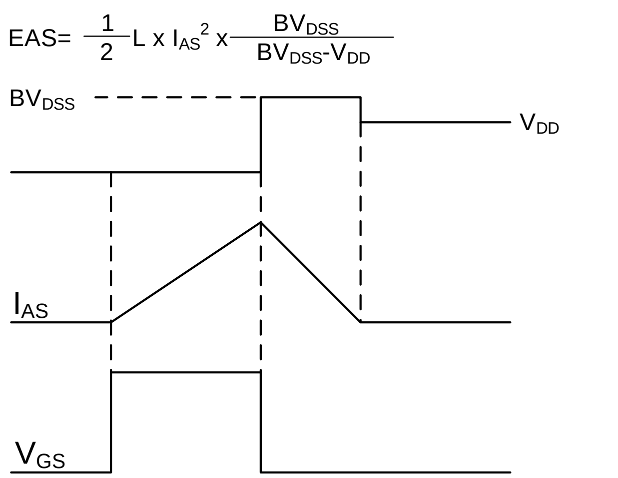
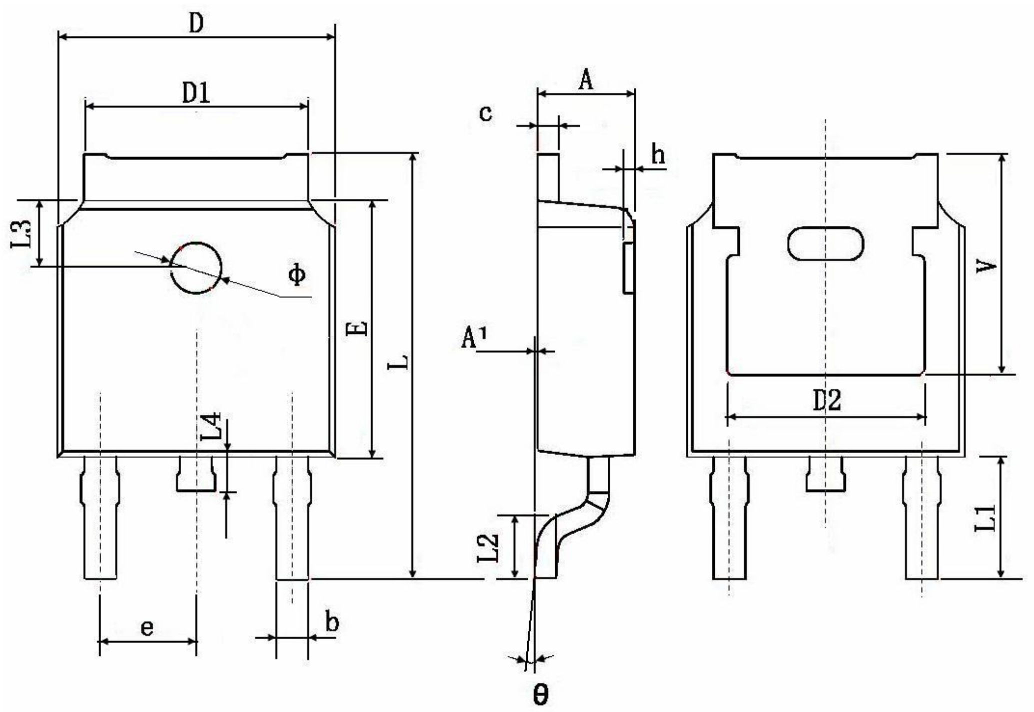


Fig.11 Unclamped Inductive Switching Waveform

TO252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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